

FUJI POWER MOSFET
Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

■ Features

High speed switching
Low on-resistance
No secondary breakdown
Low driving power
Avalanche-proof

■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

■ Maximum ratings and characteristic Absolute maximum ratings

● (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	800	V
	V _{DSX} *5	800	V
Continuous drain current	I _D	±7	A
Pulsed drain current	I _D (puls)	±28	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	I _{AR} *2	7	A
Maximum Avalanche Energy	E _{AS} *1	235.3	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt *4	40	kV/μs
Peak Diode Recovery dV/dt	dV _{DR} /dt *3	5	kV/μs
Max. power dissipation	P _D T _a =25°C	2.02	W
	T _c =25°C	195	
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C

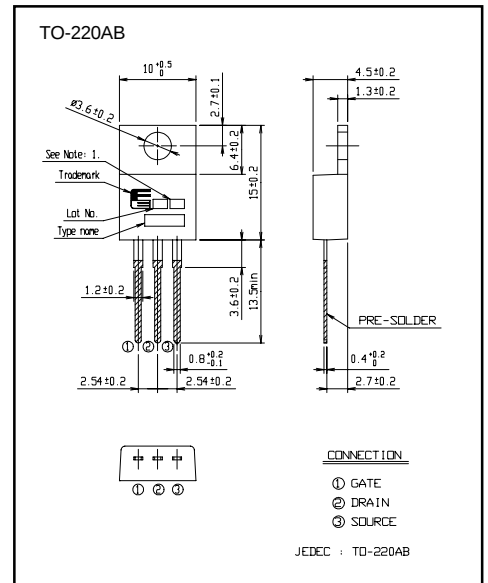
*1 L=8.8mH, V_{CC}=80V, T_{ch}=25°C See to Avalanche Energy Graph *2 T_{ch}≤150°C*3 I_F≤-I_D, -di/dt=50A/μs, V_{CC}≤B_VSS, T_{ch}≤150°C *4 V_{DS}≤800V *5 V_{GS}=-30V● Electrical characteristics (T_c=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =250μA V _{GS} =0V	800			V
Gate threshold voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =800V V _{GS} =0V			25	μA
		V _{DS} =640V V _{GS} =0V			250	
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =3.5A V _{GS} =10V		1.46	1.90	Ω
Forward transconductance	g _{fs}	I _D =3.5A V _{DS} =25V	4.1	8.2		S
Input capacitance	C _{iss}	V _{DS} =25V		740	1110	pF
Output capacitance	C _{oss}	V _{GS} =0V		105	160	
Reverse transfer capacitance	C _{rss}	f=1MHz		7	10.5	
Turn-on time t _{on}	td(on)	V _{CC} =600V I _D =3.5A		21	31.5	ns
	t _r	V _{GS} =10V		8	12	
Turn-off time t _{off}	td(off)	R _{GS} =10 Ω		40	60	
	t _f			9.6	14.4	
Total Gate Charge	Q _G	V _{CC} =400V		21.5	32	nC
Gate-Source Charge	Q _{GS}	I _D =7A		3	4.5	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		7	10.5	
Avalanche capability	I _{AV}	L=8.8mH T _{ch} =25°C	7			A
Diode forward on-voltage	V _{SD}	I _F =7A V _{GS} =0V T _{ch} =25°C		0.90	1.50	V
Reverse recovery time	t _{rr}	I _F =7A V _{GS} =0V		2.3		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		7.0		μC

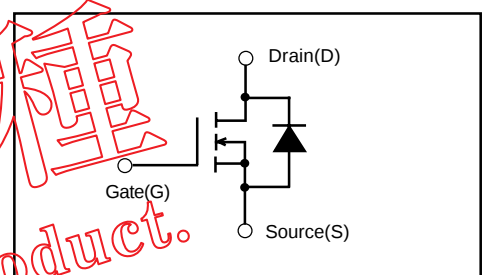
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			0.640	°C/W
	R _{th(ch-a)}	channel to ambient			62.0	°C/W

■ Outline Drawings [mm]



■ Equivalent circuit schematic



Characteristics

